

## 650V, 60A, Trench FS II Fast IGBT

### General Description

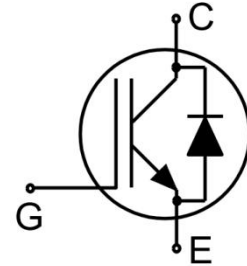
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 650V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

### Features

- Trench FSII Technology offering
- Very low  $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in  $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

### Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE60TD65BT	TO-247-3L	NCE60TD65BT



TO-247-3L

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	650	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	120	A
	Collector Current @ $T_C = 100^\circ\text{C}$	60	A
$I_{Cpuls}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	240	A
-	turn off safe operating area, $V_{CE}=650\text{V}$ , $T_j=175^\circ\text{C}$	240	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	60	A
$I_{FM}$	Diode Maximum Forward Current	240	A
$P_D$	Power Dissipation @ $T_C = 25^\circ\text{C}$	319	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	159	W
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^\circ\text{C}$
$t_{sc}$	Short circuit withstand time $V_{GE}=15\text{V}$ , $V_{CC}\leq 400\text{V}$ , Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}$ , $T_j\leq 150^\circ\text{C}$	5	$\mu\text{s}$

**Thermal Characteristic**

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.47	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	0.98	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

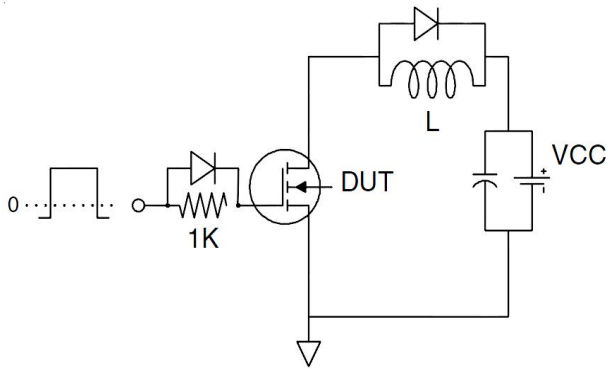
Symbol	Parameter	Conditions	Value			Units	
			Min.	Typ.	Max.		
<b>Static Characteristics</b>							
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=1mA$	650	--	--	V	
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=650V$	--	--	40	$\mu A$	
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$	--	--	200	nA	
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$	--	--	200	nA	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=50A$	$T_J=25^\circ\text{C}$	--	1.6	1.8	V
		$V_{GE}=15V$	$T_J=175^\circ\text{C}$	--	1.8	--	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=60A$	$T_J=25^\circ\text{C}$	--	1.7	1.9	V
		$V_{GE}=15V$	$T_J=175^\circ\text{C}$	--	1.9	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1mA, V_{CE}=V_{GE}$	4.0	5.0	6.0	V	
<b>Dynamic Characteristics</b>							
$C_{ies}$	Input Capacitance	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	--	7018	--	pF	
$C_{oes}$	Output Capacitance		--	199	--		
$C_{res}$	Reverse Transfer Capacitance		--	138	--		
$Q_g$	Total Gate Charge	$V_{CC}=480V, I_C=60A,$ $V_{GE}=15V$	--	262	--	nC	
$Q_{ge}$	Gate to Emitter Charge		--	60	--		
$Q_{gc}$	Gate to Collector Charge		--	113	--		
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0s$	$V_{GE}=15V, V_{CC} \leq 400V,$ $t_{SC} \leq 5\mu s, T_J \leq 150^\circ\text{C}$	--	300	--	A	
<b>Switching Characteristics</b>							
$t_{d(ON)}$	Turn-on Delay Time	$V_{CC}=400V, I_C=60A,$ $V_{GE}=0/15V, R_g=5\Omega,$ Inductive Load	--	19	--	ns	
$t_r$	Rise Time		--	17	--		
$t_{d(OFF)}$	Turn-Off Delay Time		--	170	--		
$t_f$	Fall Time		--	18	--		
$E_{on}$	Turn-On Switching Loss		$V_{CC}=400V, I_C=60A,$ $V_{GE}=0/15V, R_g=5\Omega,$ $T_J=175^\circ\text{C}$	--	1.1	--	mJ
$E_{off}$	Turn-Off Switching Loss			--	0.9	--	
$E_{ts}$	Total Switching Loss			--	2.0	--	
$E_{on}$	Turn-On Switching Loss			--	1.4	--	
$E_{off}$	Turn-Off Switching Loss	--	1.3	--	mJ		
$E_{ts}$	Total Switching Loss	--	2.7	--			

Electrical Characteristics of the Diode ( $T_c = 25^\circ\text{C}$  unless otherwise specified)

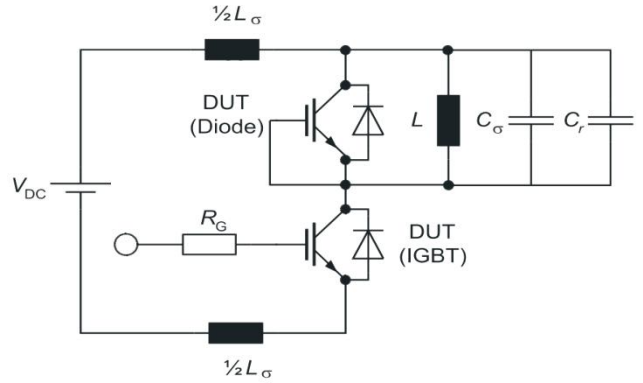
Symbol	Parameter	Conditions	Rating			Units	
			Min.	Typ.	Max.		
$V_{FM}$	Diode Forward Voltage	$I_F=50\text{A}$	$T_j=25^\circ\text{C}$	--	1.65	2.20	V
			$T_j=175^\circ\text{C}$	--	1.30	--	V
$V_{FM}$	Diode Forward Voltage	$I_F=60\text{A}$	$T_j=25^\circ\text{C}$	--	1.75	2.40	V
			$T_j=175^\circ\text{C}$	--	1.40	--	V
$T_{rr}$	Reverse Recovery Time	$I_F=60\text{A}$ , $di/dt=200\text{A}/\mu\text{s}$	--	186	--	ns	
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	3.8	--	A	
$Q_{rr}$	Reverse Recovery Charge		--	0.3	--	$\mu\text{C}$	
$T_{rr}$	Reverse Recovery Time	$I_F=60\text{A}$ , $di/dt=200\text{A}/\mu\text{s}$ , $T_j=175^\circ\text{C}$	--	458	--	ns	
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	5.3	--	A	
$Q_{rr}$	Reverse Recovery Charge		--	1.3	--	$\mu\text{C}$	

Test Circuit

1) Gate Charge Test Circuit

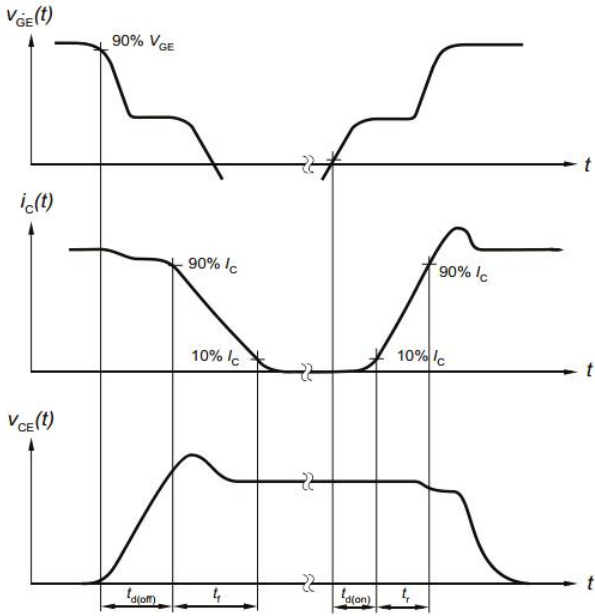


2) Switch Time Test Circuit

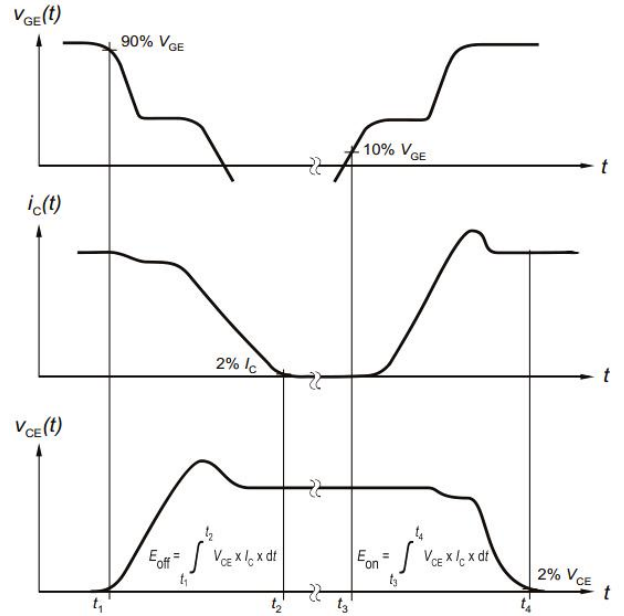


Switching characteristics

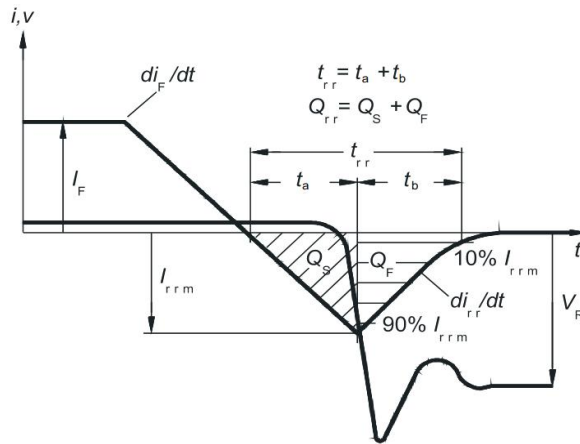
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

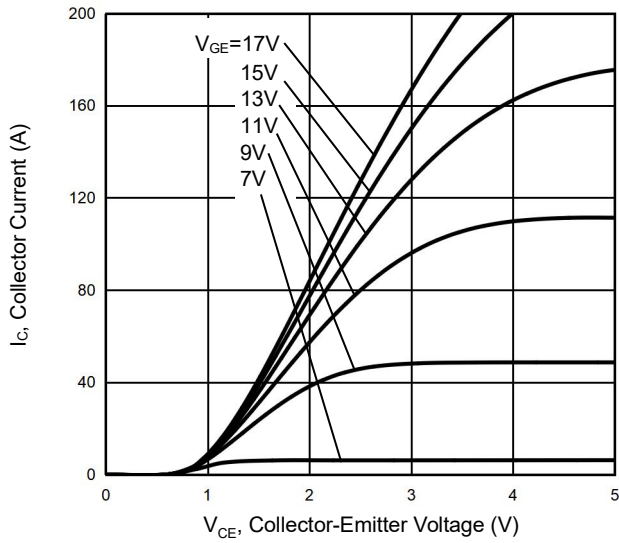


Figure 2 Output Characteristics

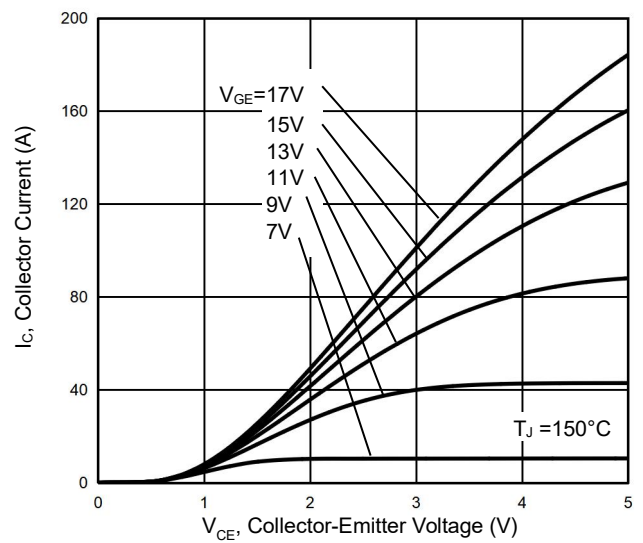


Figure 3 Transfer Characteristics

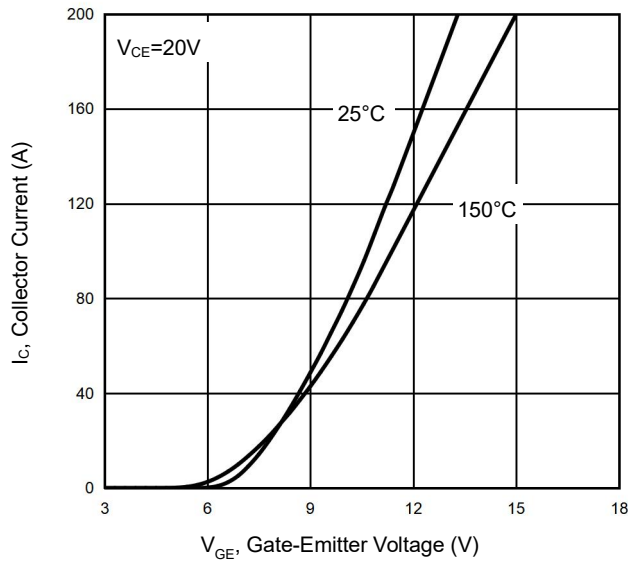


Figure 4 Saturation Voltage vs. Vge

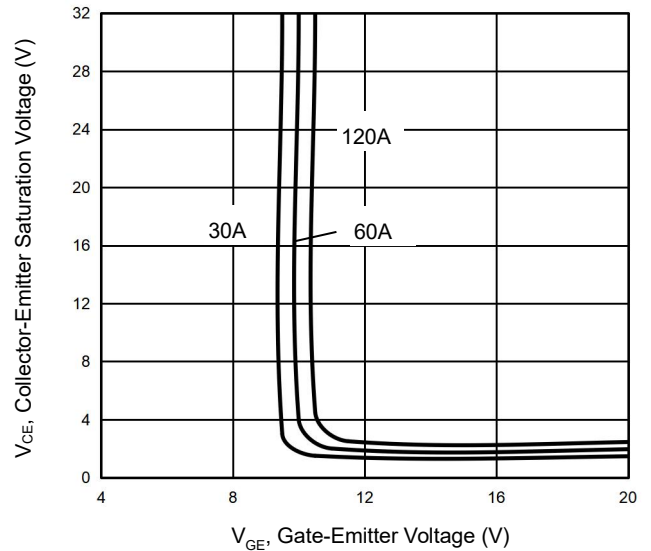


Figure 5 Capacitance Characteristics

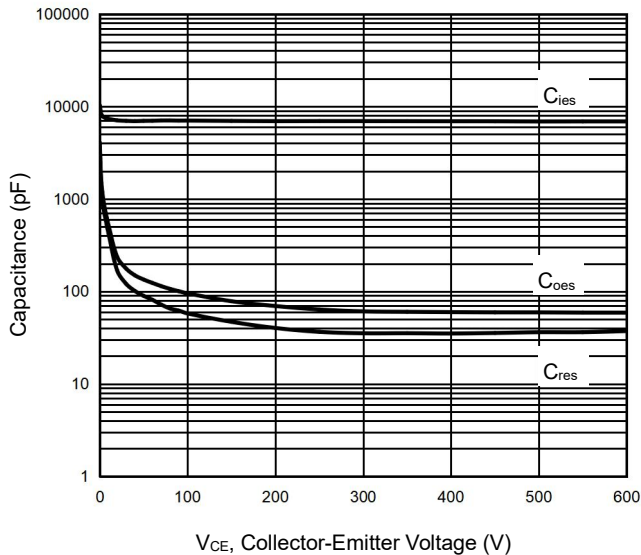
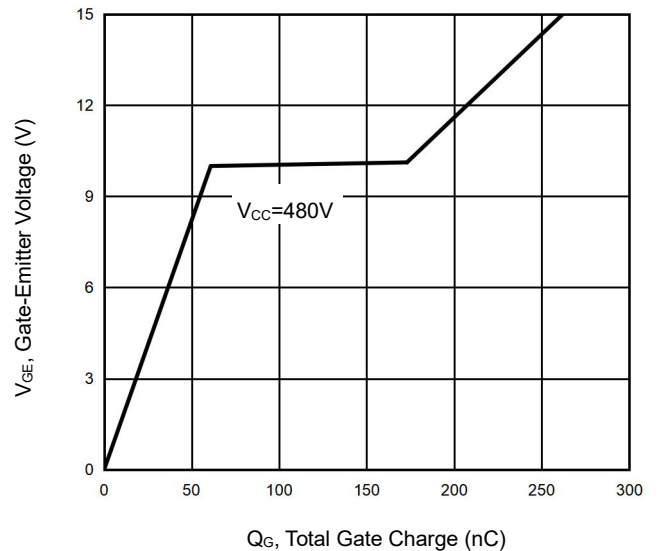


Figure 6 Gate Charge Wave Form



Typical Electrical and Thermal Characteristics

Figure 7  $V_{CE(sat)}$  vs. Case Temperature

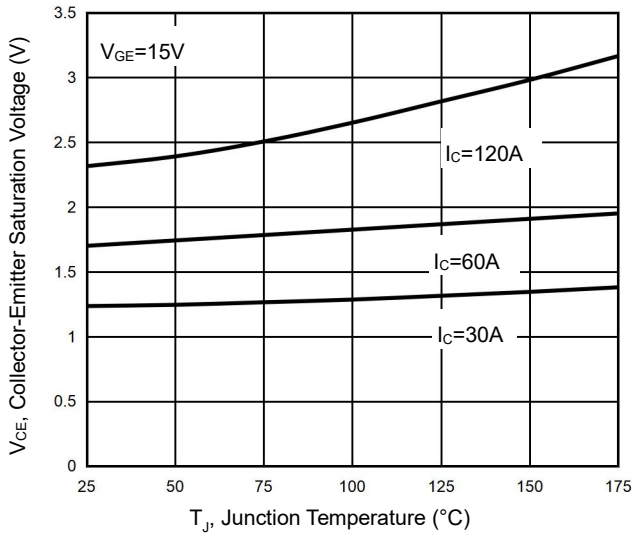


Figure 8 Typical Collector-Emitter Saturation Voltage as a function of Collector Current

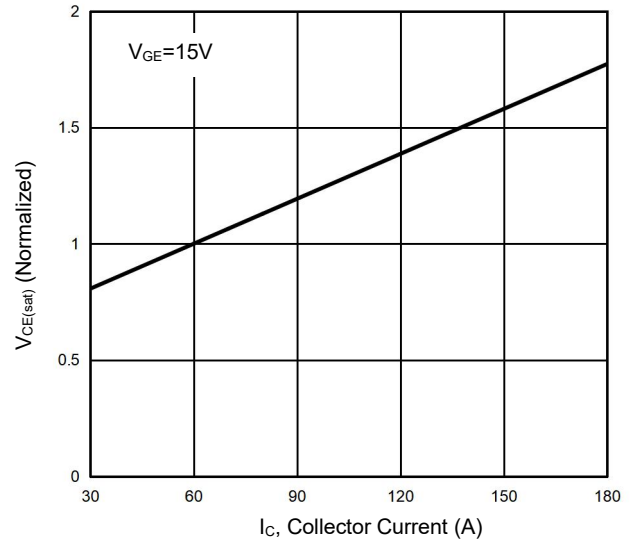


Figure 9 Forward Characteristics

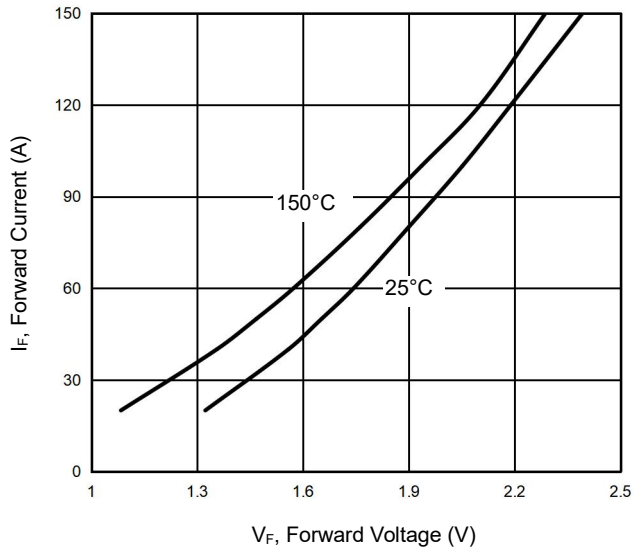


Figure 10  $V_F$  vs. Temperature

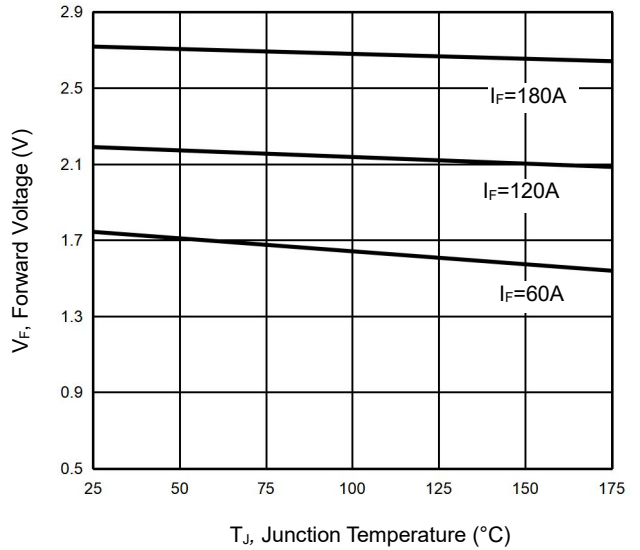


Figure 11 Switching Energy vs. Temperature

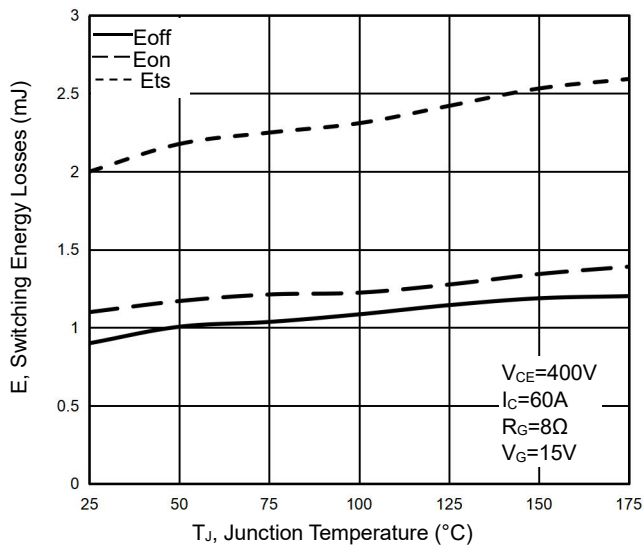
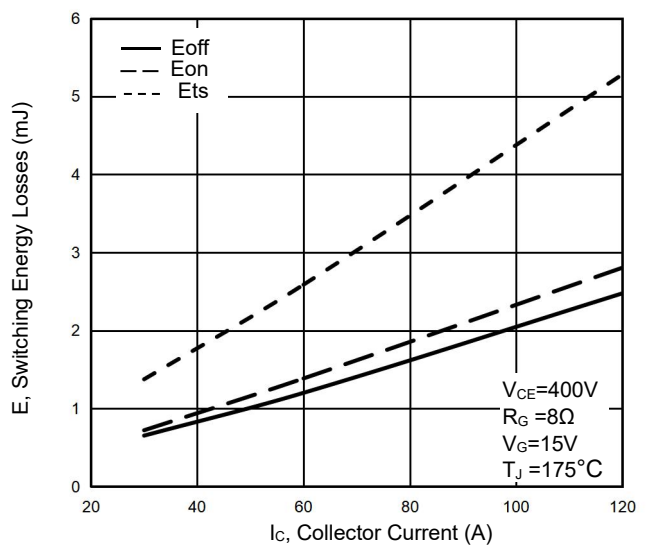


Figure 12 Switching Loss vs. Collector Current



Typical Electrical and Thermal Characteristics

Figure 13 Switching Loss vs.  $R_G$

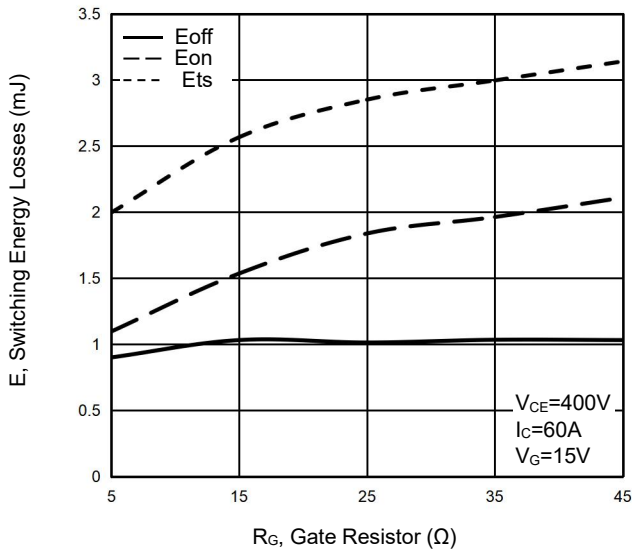


Figure 14 Switching Loss vs. Collector Current

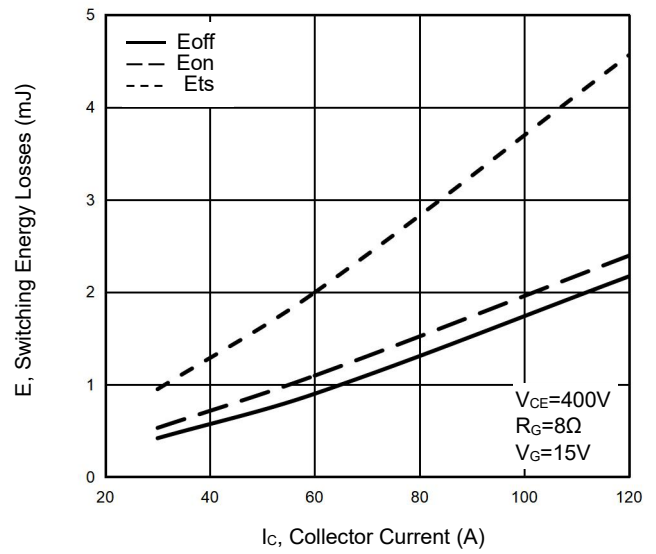


Figure 15 Forward Bias Safe Operating Area

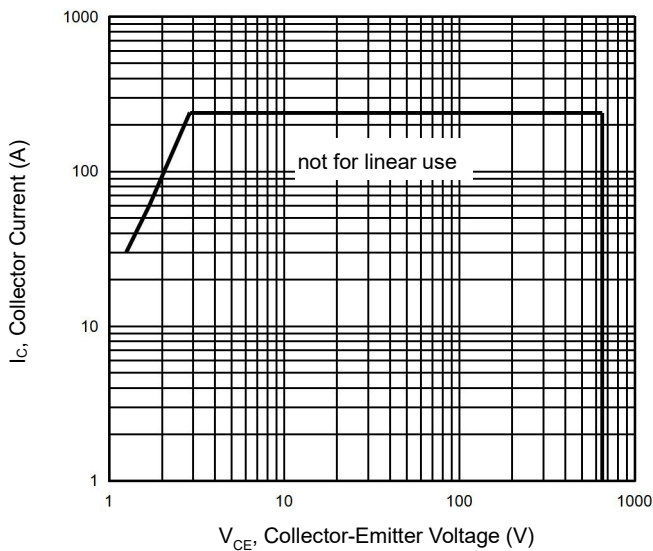


Figure 16  $P_{tot}$  vs. Case Temperature

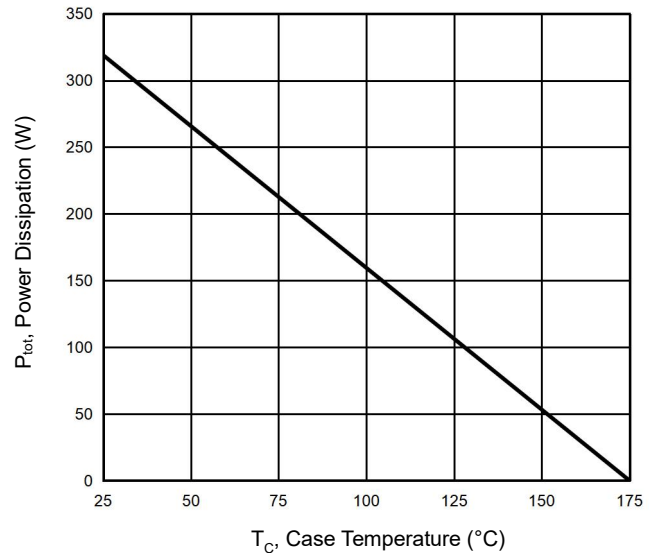


Figure 17  $V_{CES}$  vs. Case Temperature

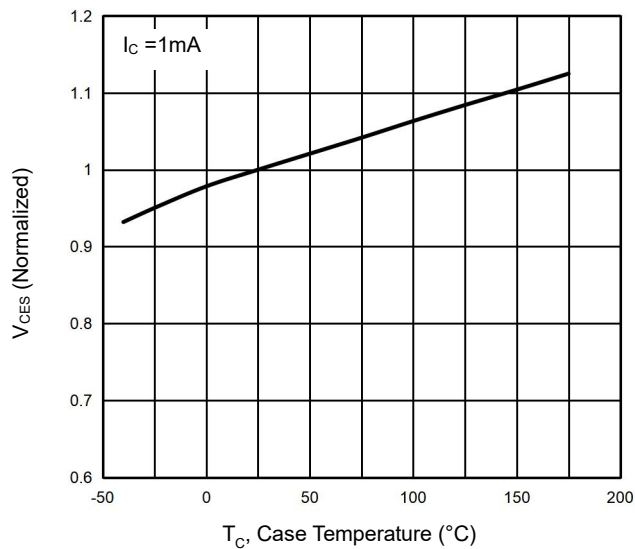
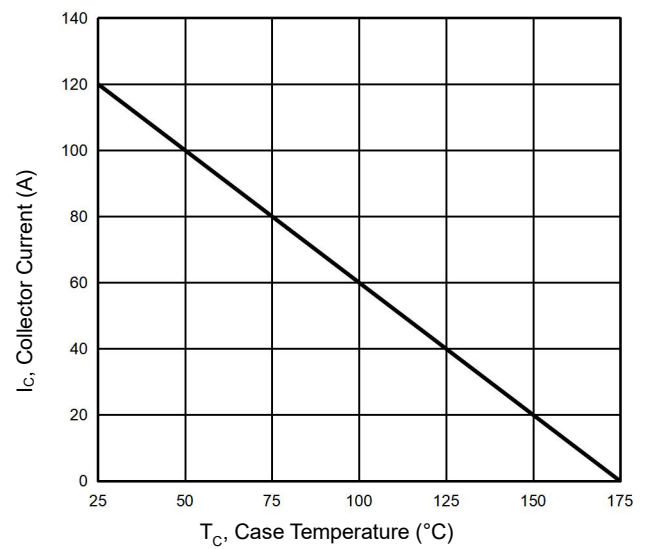
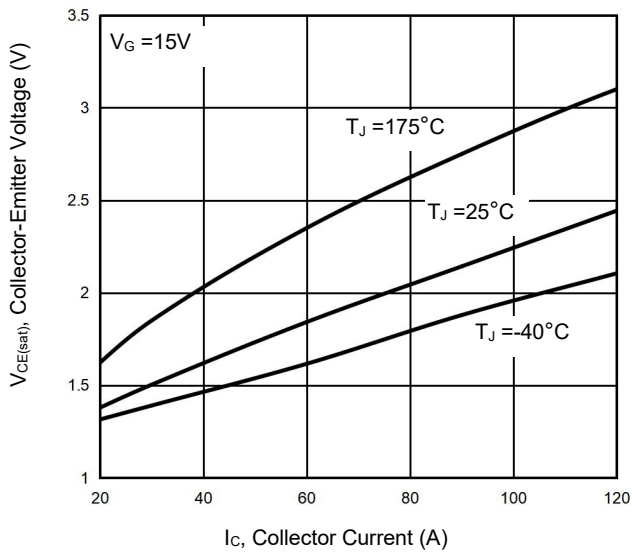


Figure 18  $I_C$  vs. Temperature

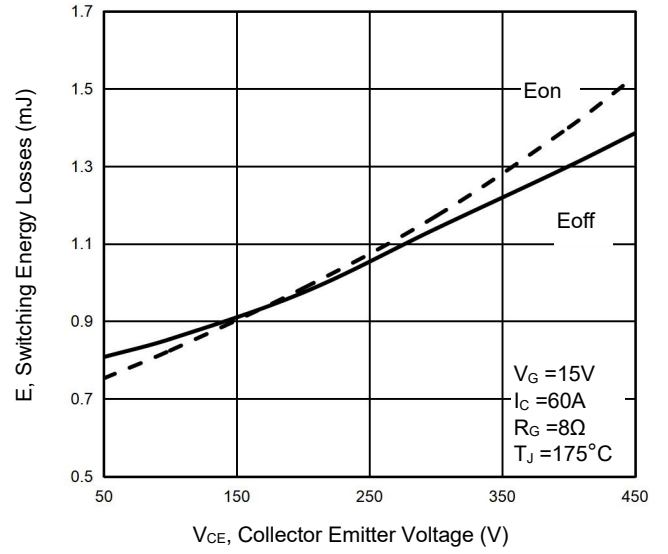


## Typical Electrical and Thermal Characteristics

**Figure 19  $V_{CE(sat)}$  vs. Collector Current**

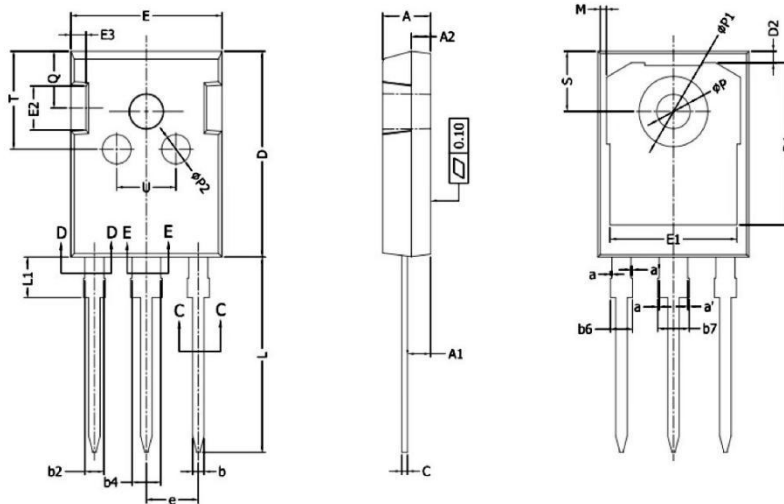


**Figure 20 Switching Loss vs.  $V_{CE}$**



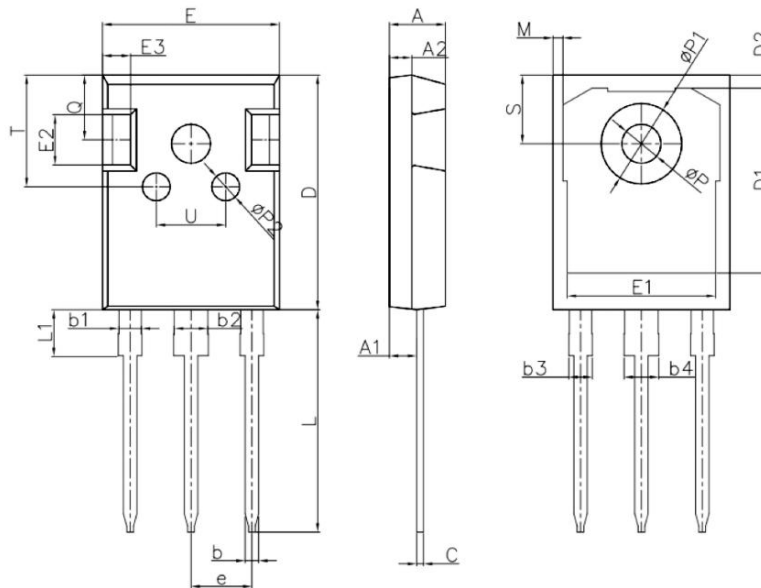


## TO-247-P Package Information



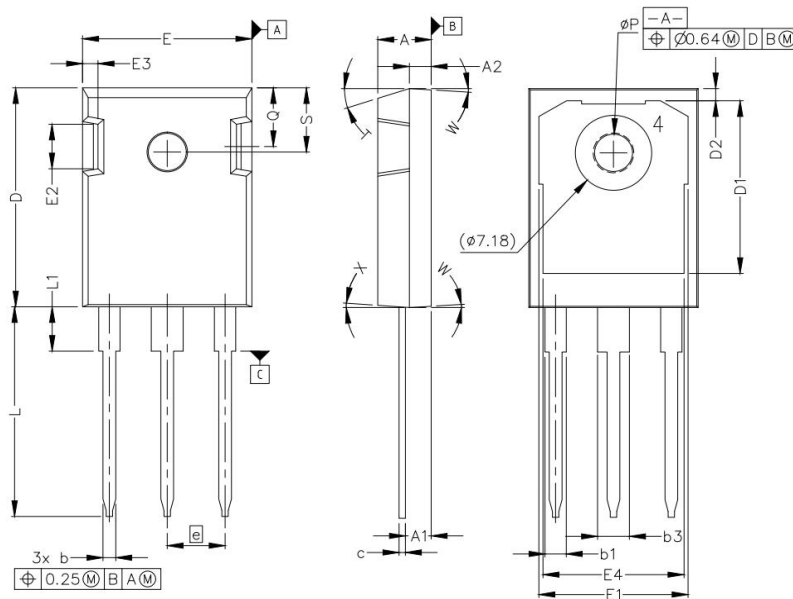
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.19	0.20
A1	2.31	2.51	0.09	0.10
A2	1.90	2.10	0.07	0.08
a	0.00	0.15	0.00	0.01
a'	0.00	0.15	0.00	0.01
b	1.16	1.26	0.04	0.05
b2	1.96	2.06	0.07	0.08
b4	2.96	3.06	0.11	0.12
b6	-	2.25	-	0.08
b7	-	3.25	-	0.12
C	0.59	0.66	0.02	0.03
D	20.90	21.10	0.82	0.83
D1	16.25	16.85	0.64	0.66
D2	1.05	1.35	0.04	0.05
E	15.70	15.90	0.61	0.62
E1	13.10	13.50	0.51	0.53
E2	4.40	4.60	0.17	0.18
E3	2.40	2.60	0.09	0.10
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.78	0.79
L1	-	4.30	-	0.16
M	0.35	0.95	0.01	0.03
P	3.40	3.60	0.13	0.14
P1	7.00	7.40	0.27	0.29
P2	2.40	2.60	0.09	0.10
Q	5.60	6.00	0.22	0.23
S	6.05	6.25	0.23	0.24
T	9.80	10.20	0.38	0.40
U	6.00	6.40	0.23	0.25

## TO-247-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.19	0.20
A1	2.31	2.51	0.09	0.10
A2	1.90	2.10	0.07	0.08
b	1.16	1.26	0.05	0.06
b1	1.96	2.06	0.08	0.09
b2	2.96	3.06	0.12	0.13
b3	--	2.25	--	0.09
b4	--	3.25	--	0.13
c	0.59	0.66	0.02	0.03
D	20.90	21.10	0.82	0.83
D1	16.25	16.85	0.64	0.66
D2	1.05	1.35	0.04	0.05
E	15.70	15.90	0.62	0.63
E1	13.10	13.50	0.52	0.53
E2	4.40	4.60	0.17	0.18
E3	2.40	2.60	0.09	0.10
e	5.436BSC		0.214BSC	
L	19.80	20.10	0.78	0.79
L1	--	4.30	--	0.17
M	0.35	0.95	0.01	0.04
P	3.40	3.60	0.13	0.14
P1	7.00	7.40	0.28	0.29
P2	2.40	2.60	0.09	0.10
Q	5.60	6.00	0.22	0.24
S	6.05	6.25	0.24	0.25
T	9.80	10.20	0.39	0.40
U	6.00	6.40	0.24	0.25

## TO-247-B Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.19	0.21
A1	2.29	2.54	0.09	0.10
A2	1.91	2.16	0.08	0.09
b	1.07	1.33	0.04	0.05
b1	1.91	2.41	0.08	0.10
b3	2.87	3.38	0.11	0.13
c	0.55	0.68	0.02	0.03
D	20.80	21.10	0.82	0.83
D1	16.25	17.65	0.64	0.70
D2	0.95	1.25	0.04	0.05
E	15.75	16.13	0.62	0.64
E1	13.10	14.15	0.52	0.56
E2	3.68	5.10	0.15	0.20
E3	1.00	1.90	0.04	0.08
E4	12.38	13.43	0.49	0.53
e	5.44 BSC		0.21 BSC	
L	19.81	20.32	0.78	0.80
L1	4.10	4.40	0.16	0.17
ØP	3.51	3.65	0.14	0.15
Q	5.49	6.00	0.22	0.24
S	6.04	6.30	0.24	0.25
T	17.5° REF			
W	3.5° REF			
X	4° REF			

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